

JG1G200F120FG

Product Preview

**1200V/200A HALF-BRIDGE MODULE WITH
FIELD-STOP TRENCH IGBT AND DIODE**

Features

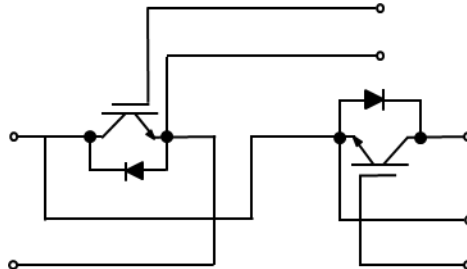
- Low $V_{CE(sat)}$
- Fast Switching
- High Ruggedness
- Short-Circuit Rated


Product Summary

V_{CES}	1200V
I_C	200A
$V_{CE(sat),typ}$	1.6V ($T_J = 25^\circ\text{C}$)

Applications

- General Purpose Inverters
- Frequency Converters
- Industrial Motor Drives
- Servos


Internal Connection


- **IGBT, Inverter**

Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit
Collector-to-Emitter Voltage	V_{CES}	1200	V
Gate-to-Emitter Voltage	V_{GES}	± 20	
Continuous DC Collector Current ($T_c = 100^\circ\text{C}$, $T_J = 175^\circ\text{C}$)	I_{CDC}	200	A
Repetitive Peak Collector Current ($t_p=1\text{ms}$)	I_{CRM}	400	
Maximum Power Dissipation ($T_c = 25^\circ\text{C}$, $T_J = 175^\circ\text{C}$)	$P_{D(max)}$	1000	W

Electrical Characteristics ^{(1), (2)}

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Collector-to-Emitter Breakdown Voltage	BV_{CES}	$V_{GE} = 0V, I_C = 250\mu A$	1200	-	-	V	
Collector-to-Emitter Leakage Current	I_{CES}	$V_{CE} = 1200V, V_{GE} = 0V$	-	-	5	mA	
Gate-to-Emitter Leakage Current	I_{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$	-	-	400	nA	
Gate Threshold Voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C = 1.5mA$	5.5	6.5	7.5	V	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C = 200A$	-	1.6	2.0		
		$V_{GE} = 15V, I_C = 200A, T_J = 125^\circ C$	-	2.0	-		
		$V_{GE} = 15V, I_C = 200A, T_J = 150^\circ C$	-	2.05	-		
Total Gate Charge	Q_g	$V_{CC} = 600V, V_{GE} = 0/15V, I_C = 200A$	-	0.96	-	μC	
Internal Gate Resistance	R_{Gint}	-	-	2.0	-	Ω	
Input Capacitance	C_{iss}	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$	-	19.5	-	nF	
Output Capacitance	C_{oss}		-	1.0	-		
Reverse Transfer Capacitance	C_{riss}		-	0.28	-		
Turn-on Delay time	$t_{d(ON)}$	$V_{CC} = 600V, V_{GE} = 0/15V, R_G = 2\Omega, I_C = 200A, L_{load} = 0.82mH,$ Energy losses include "tail" and diode reverse recovery.	-	83	-	ns	
Rise Time	t_r		-	75	-		
Turn-off Delay time	$t_{d(OFF)}$		-	307	-		
Fall Time	t_f		-	88	-		
Turn-On Switching Loss	E_{on}		-	-	16.5	-	mJ
Turn-Off Switching Loss	E_{off}			-	8.0	-	
IGBT Total Switching Loss	E_{ts}			-	24.5	-	
Turn-on Delay time	$t_{d(ON)}$	$V_{CC} = 600V, V_{GE} = 0/15V, R_G = 2\Omega, I_C = 200A, L_{load} = 0.82mH,$ Energy losses include "tail" and diode reverse recovery. $T_J = 150^\circ C$	-	93	-	ns	
Rise Time	t_r		-	95	-		
Turn-off Delay time	$t_{d(OFF)}$		-	396	-		
Fall Time	t_f		-	140	-		
Turn-On Switching Loss	E_{on}		-	-	28.1	-	mJ
Turn-Off Switching Loss	E_{off}			-	13.9	-	
IGBT Total Switching Loss	E_{ts}			-	42	-	
Short Circuit Collector Current	$I_{C(SC)}$	$V_{GE} = 15V, V_{CC} \leq 600V, t_{SC} \leq 10\mu s$	-	750	-	A	

- **Diode, Inverter**

Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	1200	V
Continuous DC Forward Current ($T_c = 100\text{ }^\circ\text{C}$, $T_j = 150\text{ }^\circ\text{C}$)	I_F	200	A
Repetitive Peak Forward Current ($t_p=1\text{ms}$)	I_{FRM}	400	

Electrical Characteristics ⁽¹⁾

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Diode Forward Voltage	V_F	$I_F = 200\text{A}$	-	1.8	2.15	V
		$I_F = 200\text{A}$ $T_j = 125\text{ }^\circ\text{C}$	-	1.55	-	
		$I_F = 200\text{A}$ $T_j = 150\text{ }^\circ\text{C}$	-	1.5	-	
Diode Reverse-Recovery Charge	Q_{rr}	$V_R = 600\text{V}$, $I_F = 200\text{A}$, $di_F/dt = -2116\text{ A}/\mu\text{s}$	-	16.4	-	μC
Diode Peak Reverse-Recovery Current	I_{rrm}		-	113	-	A
Diode Reverse-Recovery Loss	E_{rr}		-	5.4	-	mJ

- **Module**

Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit
Maximum Junction Temperature	T_j	-40 to +175	$^\circ\text{C}$
Operating Junction Temperature	$T_{vj\text{ op}}$	-40 to +150	
Storage Temperature	T_{stg}	-40 to +125	
Isolation Voltage ($f = 50\text{ Hz}$, $t = 1\text{ min}$)	V_{iso}	2.5	kV

Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Material of Module Baseplate	-	-	Cu	-	-
Internal Isolation	-	-	Al_2O_3	-	-
Creepage Distance, Terminal to Heatsink	-	-	29	-	mm
Creepage Distance, Terminal to Terminal	-	-	23	-	mm

Clearance, Terminal to Heatsink	-	-	23	-	mm
Clearance, Terminal to Terminal	-	-	11	-	mm
Stray Inductance, Module	L_{SCE}	-	20	-	nH
Module Lead Resistance, Terminal to Chip	$R_{CC'+EE'}$	-	0.7	-	m Ω
Junction-to-Case Thermal Resistance, per IGBT, Inverter	$R_{\theta JC}$	-	0.12	-	$^{\circ}\text{C}/\text{W}$
Junction-to-Case Thermal Resistance, per Diode, Inverter		-	0.18	-	
Case-to-Heatsink Thermal Resistance, per IGBT, Inverter	$R_{\theta CH}$	-	0.034	-	$^{\circ}\text{C}/\text{W}$
Case-to-Heatsink Thermal Resistance, per Diode, Inverter		-	0.05	-	
Case-to-Heatsink Thermal Resistance, per Module		-	0.01	-	
Mounting Torque for Module Mounting, Screw M6	M	3.0	-	6.0	Nm
Terminal Connection Torque, Screw M6	M	2.5	-	5.0	Nm
Weight per Module	G	-	320	-	g

(1) $T_j = 25^{\circ}\text{C}$ unless otherwise specified

(2) t_r : from 10% of I_c to 90% of I_c ; t_f : from 90% of I_c to 10% of I_c ;

E_{on} : from 10% of V_{GE} to 10% of V_{CE} ; E_{off} : from 90% of V_{GE} to 10% of I_c .

• **Typical Electrical Characteristics**

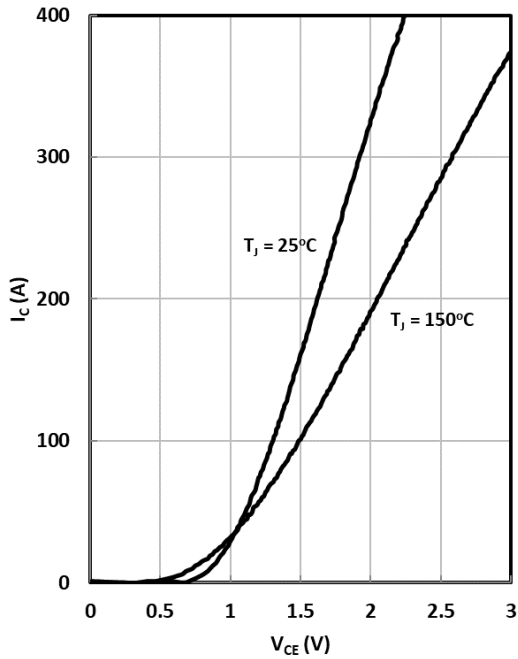


Fig. 1 IGBT (Inverter) Output Characteristics

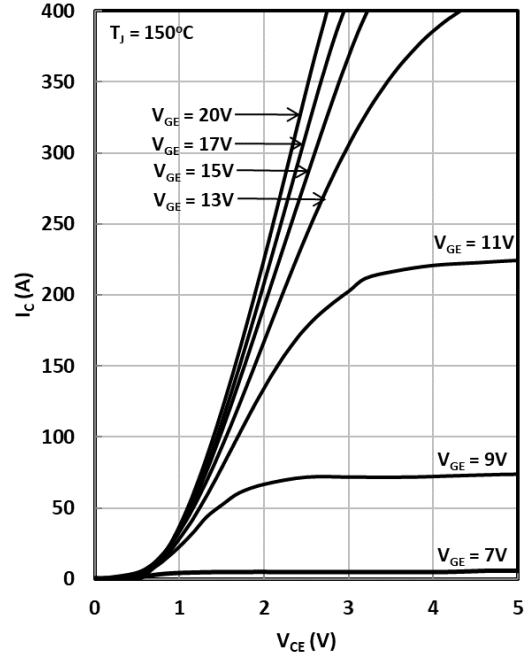


Fig. 2 IGBT (Inverter) Output Characteristics

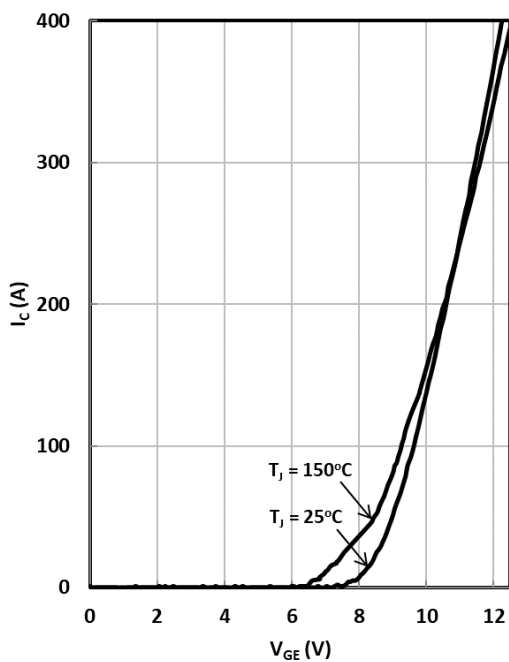


Fig. 3 IGBT (Inverter) Transfer Characteristics

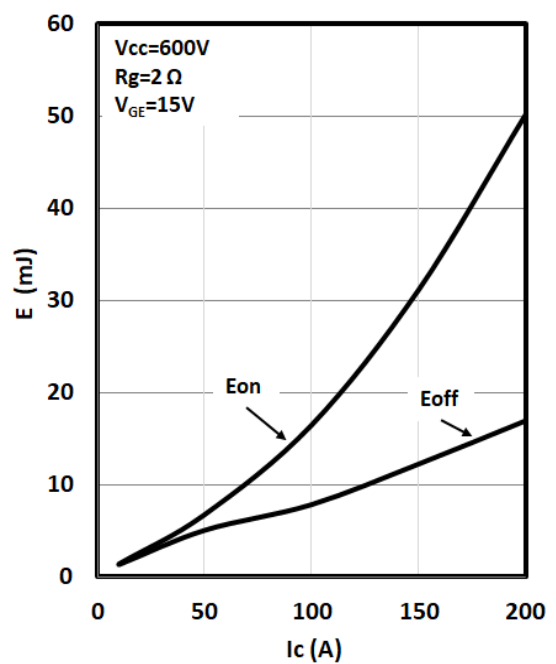


Fig. 4 IGBT (Inverter) Switching Loss vs. Ic

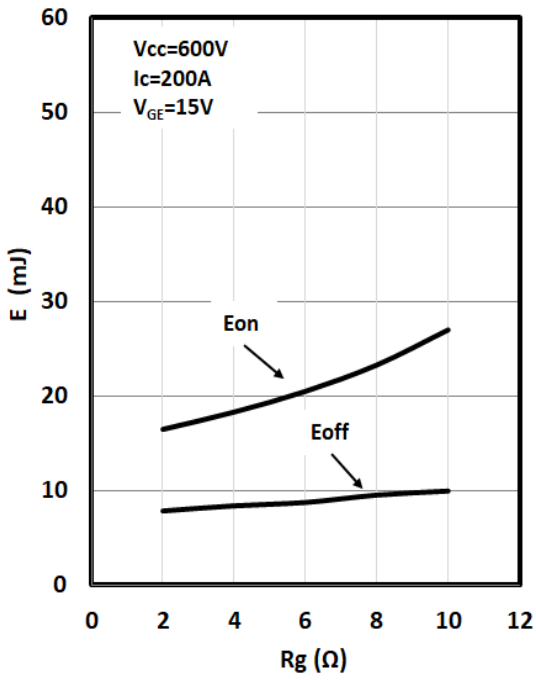


Fig. 5 IGBT (Inverter) Switching Loss vs. R_g

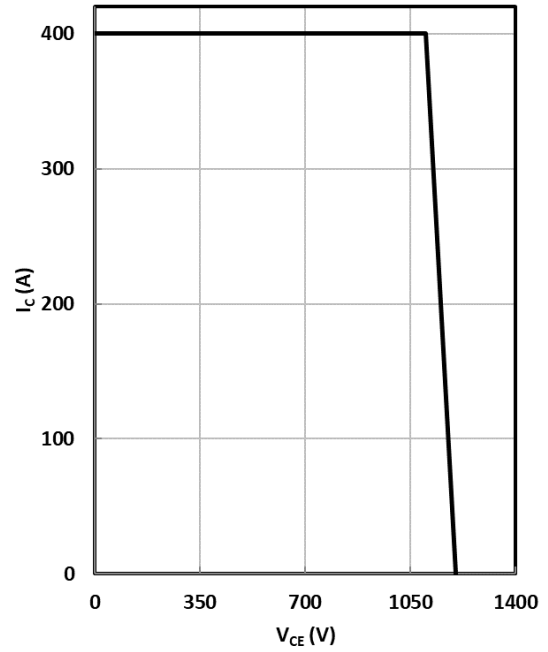


Fig. 6 RBSOA

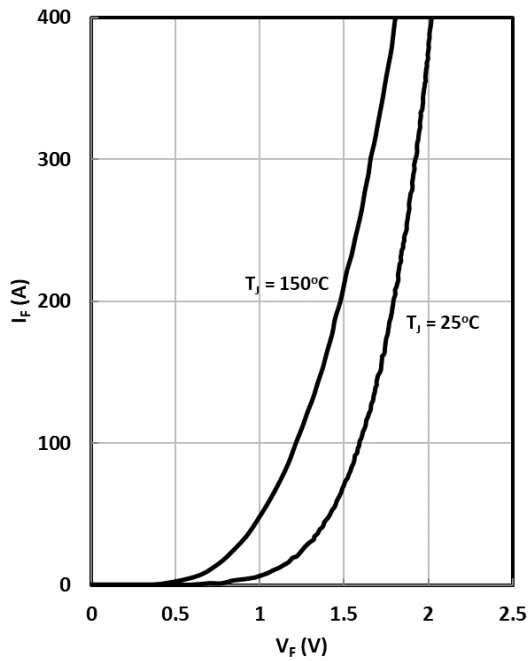
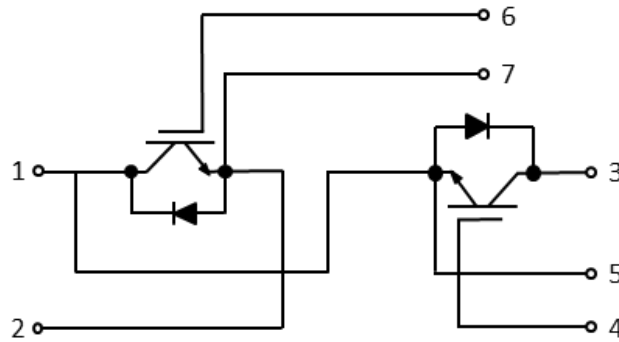
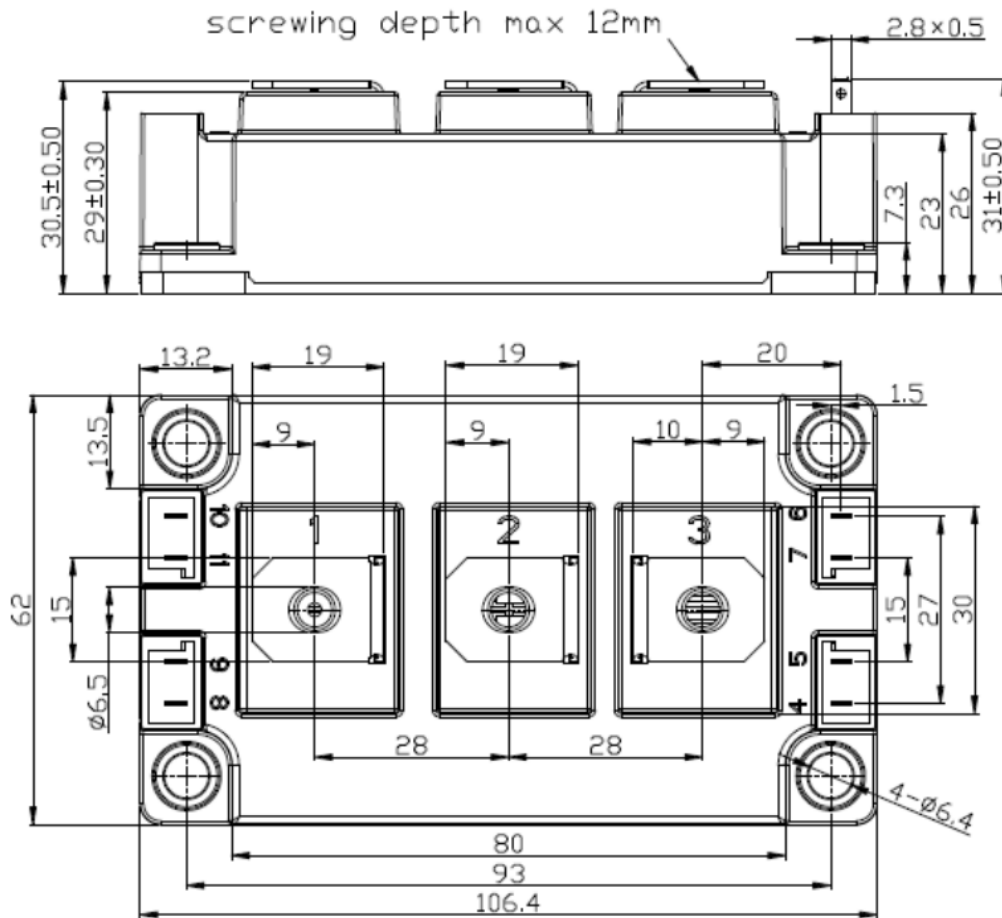


Fig. 7 Diode (Inverter) Forward Characteristics

- Circuit diagram



- Package Dimensions



Revision history of JG1G200F120FG Specification

Version	Change Items	Effective Date
1.00	Initial Release	Apr-2021

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